What is claimed is:

1. A method of forming a via hole through a glass wafer, comprising:

depositing a material layer on an outer surface of the glass wafer, the material layer having a selection ratio higher than that of the glass wafer;

forming a via-patterned portion on one side of the material layer;

performing a first etching in which the via-patterned portion is etched to form a preliminary via hole;

eliminating any remaining patterning material used in the formation of the via-patterned portion;

performing a second etching in which the preliminary via hole is etched to form a via hole having a smooth surface and extending through the glass wafer; and

eliminating the material layer.

2. The method as claimed in claim 1, wherein the material layer is formed of polysilicon.

3. The method as claimed in claim 1, wherein the first etching is performed by sandblasting.

4. The method as claimed in claim 1, wherein the first etching is performed by a device selected from the group consisting of: an ultrasonic wave, a drill, and a laser beam.

5. The method as claimed in claim 1, wherein, during the first etching, the via-patterned portion is etched to a sufficient depth so that the preliminary via hole has a bottom adjacent to another side of the material layer opposite to the via-patterned portion.

6. The method as claimed in claim 1, wherein forming a via-patterned portion on one side of the material layer comprises:

laminating a film resistor on an upper surface of the material layer; and

exposing and developing the film resistor to form the via-patterned portion on one side of the material layer.

7. The method as claimed in claim 6, wherein the film resistor comprises a material having a large resistance to sandblast etching to permit the film resistor to function as a protection film during subsequent sandblasting of the glass wafer.

8. The method as claimed in claim 1, wherein the second etching is a wet etching.

9. The method as claimed in claim 8, wherein the wet etching uses a hydrofluoric acid (HF) solution.